ABSTRACT

There is provided a technique that includes a first opening and a second opening which supply gases to a process chamber in which a substrate is arranged, and is configured such that: the first opening and the second opening are arranged in a direction parallel to a surface of the substrate, a gas supplied from the first opening is supplied toward a center of the substrate, a gas supplied from the second opening is supplied toward a peripheral edge of the substrate, and a direction of the gas supplied from the second opening forms a predetermined angle with respect to a direction of the gas supplied from the first opening.

FIG. 1